

(b) Amendments to the Claims

Please amend claims 17 and 18 as follows. A detailed listing of the claims is provided.

1 - 16 (Cancelled)

17. (Currently Amended) An accumulated film forming apparatus for continuously accumulating a plurality of semiconductor layers on a long substrate by the plasma CVD method, characterized by, in order, at least a first chamber for forming an n-type semiconductor layer, a second chamber for forming a non-crystalline i-type semiconductor layer, a first third accumulation chamber for making an a microcrystalline i-type layer having means for making raw material gas flow from the upper part toward the lower part in the direction movement of said long substrate and a ~~second~~ fourth accumulation chamber for making a p-type layer on said microcrystalline i-type layer having means for making the raw material gas containing a p-type dopant flow from the lower part toward the upper part in the direction of movement of said long substrate, said ~~first third~~ accumulation chamber and said ~~second~~ fourth accumulation chamber being connected together by ~~a separating path, said separation path being~~ a gas gate introducing means to prevent diffusion of said gas containing said p-type dopant in said ~~second~~ fourth accumulation chamber from diffusing into the ~~first third~~ accumulation chamber.

18. (Currently Amended) An accumulation film forming apparatus according to claim 17, characterized in that the area of an electrode in at least said ~~second~~

fourth accumulation chamber for applying electric power for causing plasma is larger than the area of said long substrate in said accumulation chamber.

19. (Original) An accumulated film forming apparatus according to claim 19, characterized in that said electrode is fin-shaped.

20. (Original) An accumulated film forming apparatus according to claim 18, characterized in that said electrode is enclosure-shaped.

21. (Original) An accumulated film forming apparatus according to claim 18, characterized in that the potential of said electrode is positive relative to said long substrate.

22. (Original) An accumulated film forming apparatus according to claim 17, characterized in that a portion for supplying said raw material gas into said accumulation chambers has a member for shielding said long substrate from the flow of said raw material gas.

23. - 27. (Cancelled)